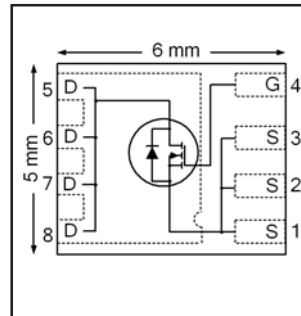


HEXFET® Power MOSFET

$V_{DS}$	<b>150</b>	<b>V</b>
$R_{DS(on) max}$ (@ $V_{GS} = 10V$ )	<b>31</b>	<b>mΩ</b>
$Q_g$ (typical)	<b>36</b>	<b>nC</b>
$R_G$ (typical)	<b>1.7</b>	<b>Ω</b>
$I_D$ (@ $T_{mb} = 25°C$ )	<b>44</b>	<b>A</b>



**Applications**

- Primary Side Synchronous Rectification
- Inverters for DC Motors
- DC-DC Brick Applications
- Boost Converters

**Features and Benefits**

**Features**

Low $R_{DS(on)}$ (< 31 mΩ)
Low Thermal Resistance to PCB (<0.8°C/W)
100% $R_g$ tested
Low Profile (<0.9 mm)
Industry-Standard Pinout
Compatible with Existing Surface Mount Techniques
RoHS Compliant Containing no Lead, no Bromide and no Halogen
MSL1, Industrial Qualification

**Benefits**

Lower Conduction Losses
Increased Power Density
Increased Reliability
Increased Power Density
Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

results in  
⇒

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFH5015PBF	PQFN 5mm x 6mm	Tape and Reel	4000	IRFH5015TRPBF

**Absolute Maximum Ratings**

	Parameter	Max.	Units
$V_{DS}$	Drain-to-Source Voltage	150	V
$V_{GS}$	Gate-to-Source Voltage	± 20	
$I_D$ @ $T_A = 25°C$	Continuous Drain Current, $V_{GS}$ @ 10V	10	A
$I_D$ @ $T_A = 70°C$	Continuous Drain Current, $V_{GS}$ @ 10V	8.2	
$I_D$ @ $T_{mb} = 25°C$	Continuous Drain Current, $V_{GS}$ @ 10V	44	
$I_D$ @ $T_{mb} = 100°C$	Continuous Drain Current, $V_{GS}$ @ 10V	28	
$I_{DM}$	Pulsed Drain Current ①	220	W
$P_D$ @ $T_A = 25°C$	Power Dissipation ⑤	3.6	
$P_D$ @ $T_{mb} = 25°C$	Power Dissipation ⑤	156	
	Linear Derating Factor ⑤	0.029	W/°C
$T_J$ $T_{STG}$	Operating Junction and Storage Temperature Range	-55 to + 150	°C

Notes ① through ⑤ are on page 9

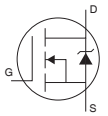
**Static @ T<sub>J</sub> = 25°C (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	150	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	0.12	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1.0mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	25.5	31	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 34A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	3.0	—	5.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 150μA
ΔV <sub>GS(th)</sub>	Gate Threshold Voltage Coefficient	—	-12	—	mV/°C	
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	20	μA	V <sub>DS</sub> = 150V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 150V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V
g <sub>fs</sub>	Forward Transconductance	38	—	—	S	V <sub>DS</sub> = 50V, I <sub>D</sub> = 34A
Q <sub>g</sub>	Total Gate Charge	—	36	54	nC	V <sub>DS</sub> = 75V V <sub>GS</sub> = 10V I <sub>D</sub> = 34A
Q <sub>gs1</sub>	Pre-V <sub>th</sub> Gate-to-Source Charge	—	13	—		
Q <sub>gs2</sub>	Post-V <sub>th</sub> Gate-to-Source Charge	—	4.6	—		
Q <sub>gd</sub>	Gate-to-Drain Charge	—	11	—		
Q <sub>godr</sub>	Gate Charge Overdrive	—	7.4	—		
Q <sub>sw</sub>	Switch Charge (Q <sub>gs2</sub> + Q <sub>gd</sub> )	—	15.6	—		
Q <sub>oss</sub>	Output Charge	—	14	—	nC	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
R <sub>G</sub>	Gate Resistance	—	1.7	—	Ω	
t <sub>d(on)</sub>	Turn-On Delay Time	—	9.4	—	ns	V <sub>DD</sub> = 75V, V <sub>GS</sub> = 10V I <sub>D</sub> = 34A R <sub>G</sub> = 1.3Ω
t <sub>r</sub>	Rise Time	—	9.7	—		
t <sub>d(off)</sub>	Turn-Off Delay Time	—	14	—		
t <sub>f</sub>	Fall Time	—	3.4	—		
C <sub>iss</sub>	Input Capacitance	—	2300	—	pF	V <sub>GS</sub> = 0V V <sub>DS</sub> = 50V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	205	—		
C <sub>rss</sub>	Reverse Transfer Capacitance	—	47	—		

**Avalanche Characteristics**

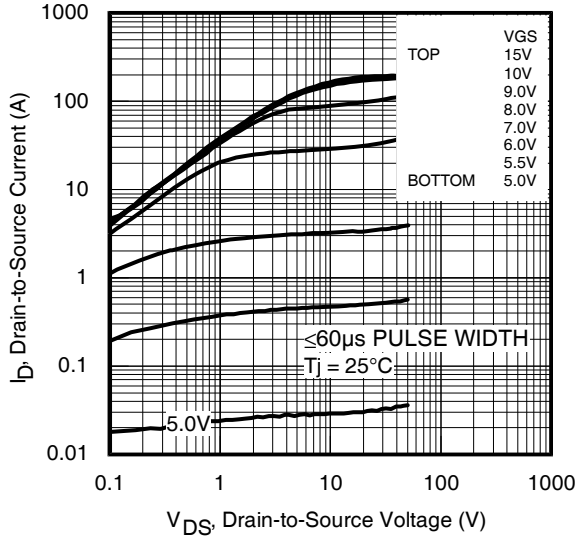
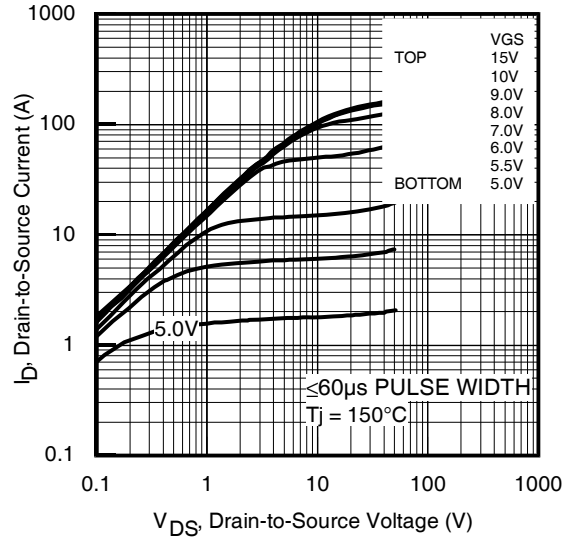
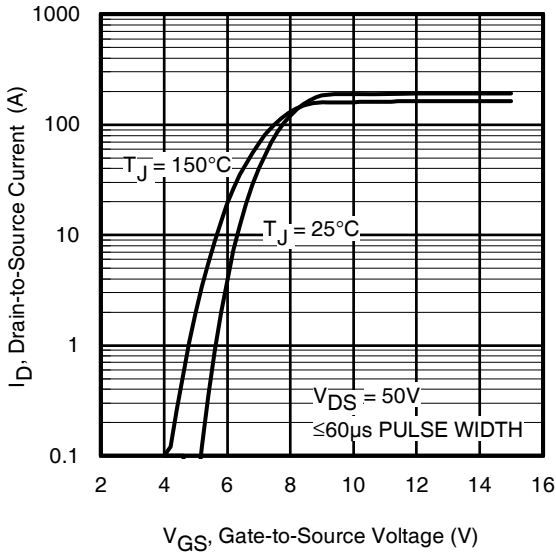
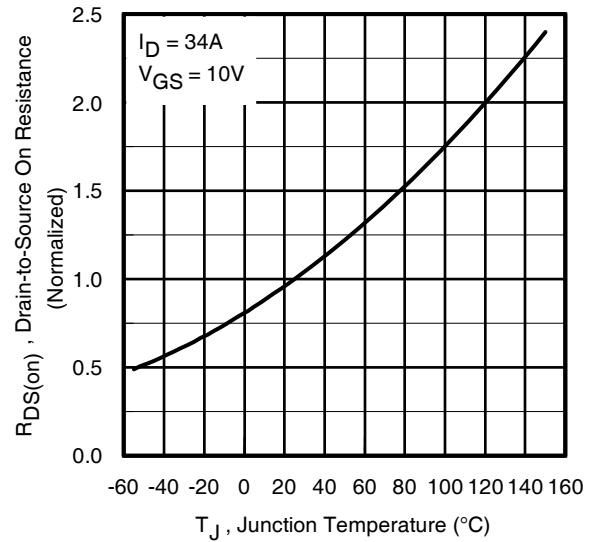
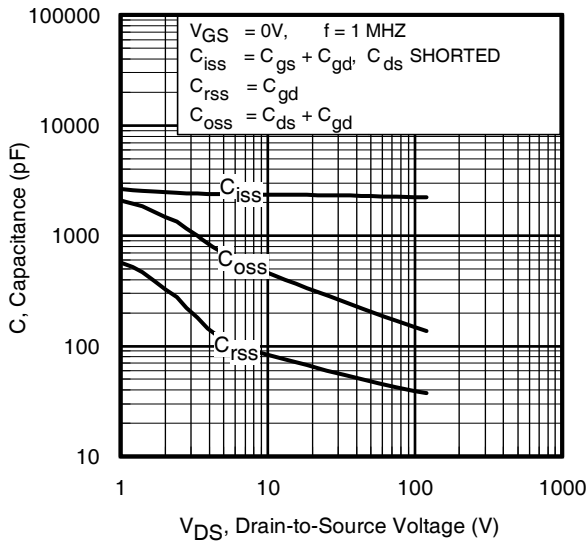
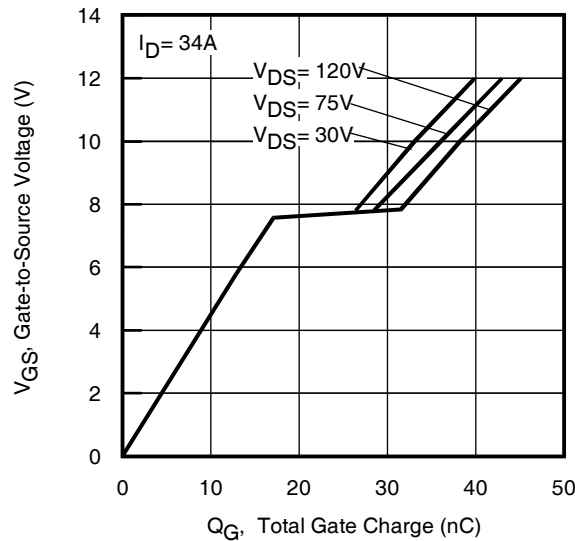
	Parameter	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy ②	—	230	mJ
I <sub>AR</sub>	Avalanche Current ①	—	34	A

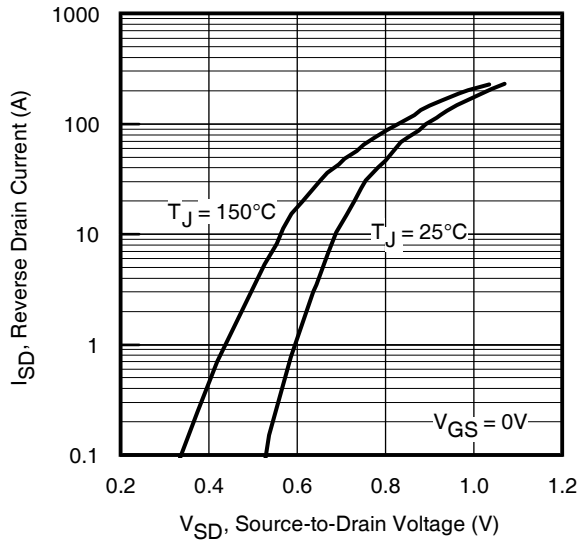
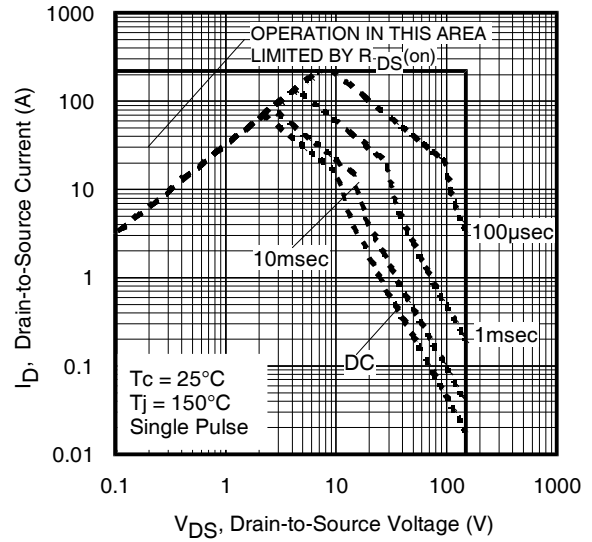
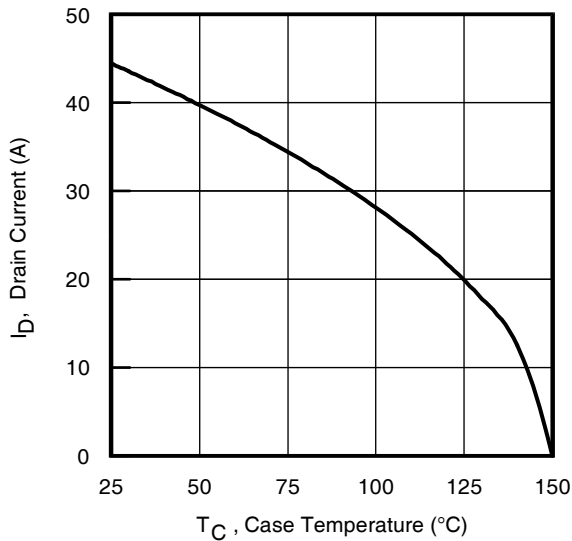
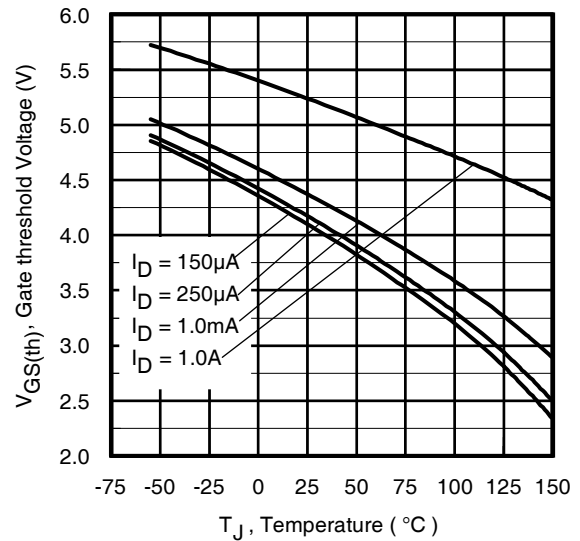
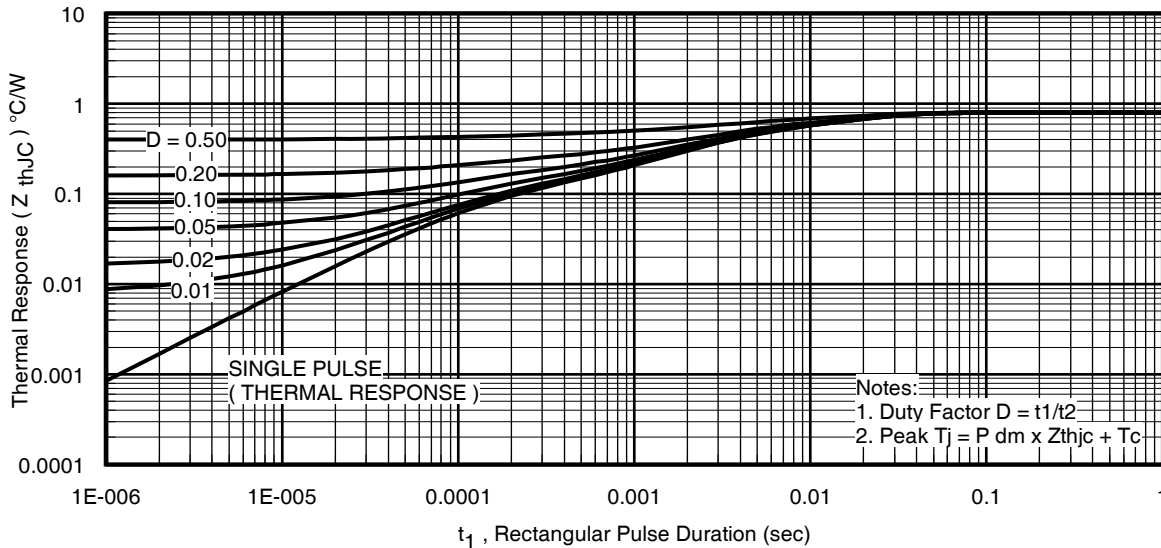
**Diode Characteristics**

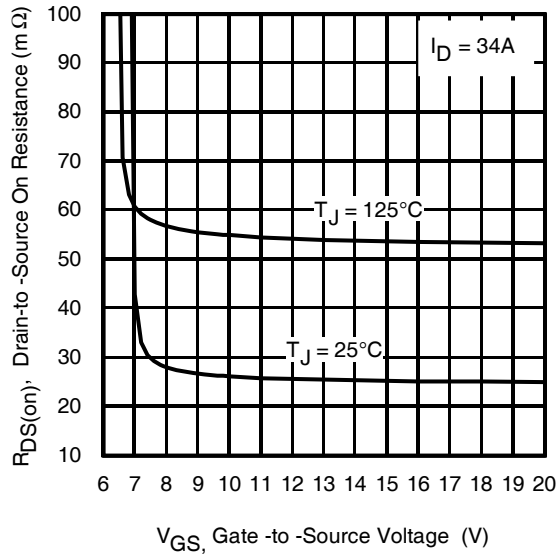
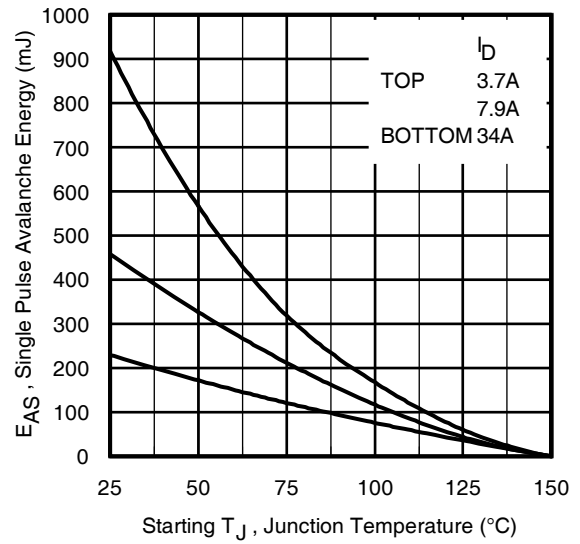
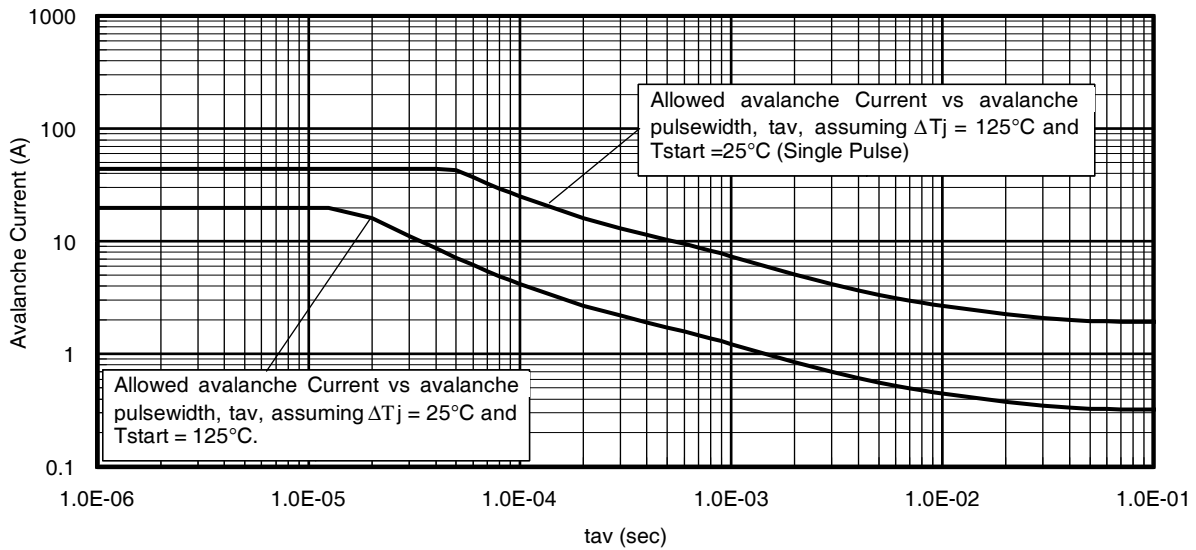
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	56	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	220		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 34A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	52	78	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 34A, V <sub>DD</sub> = 75V
Q <sub>rr</sub>	Reverse Recovery Charge	—	550	825	nC	di/dt = 500A/μs ③
t <sub>on</sub>	Forward Turn-On Time	Time is dominated by parasitic Inductance				

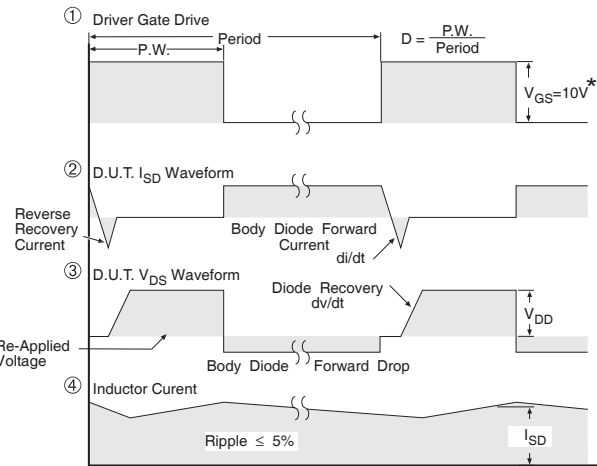
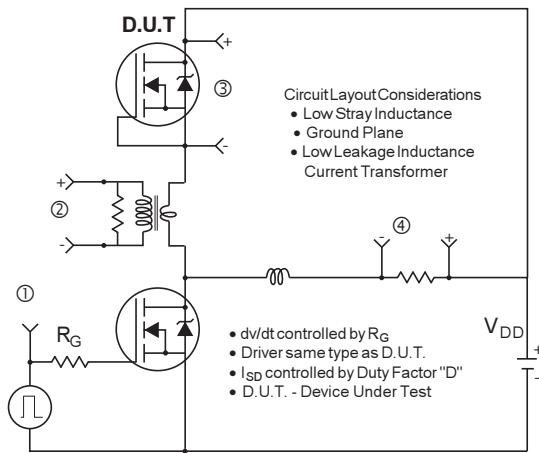
**Thermal Resistance**

	Parameter	Typ.	Max.	Units
R <sub>θJC-mb</sub>	Junction-to-Mounting Base	0.5	0.8	°C/W
R <sub>θJC</sub> (Top)	Junction-to-Case ④	—	15	
R <sub>θJA</sub>	Junction-to-Ambient ⑤	—	35	
R <sub>θJA</sub> (<10s)	Junction-to-Ambient ⑤	—	22	


**Fig 1. Typical Output Characteristics**

**Fig 2. Typical Output Characteristics**

**Fig 3. Typical Transfer Characteristics**

**Fig 4. Normalized On-Resistance vs. Temperature**

**Fig 5. Typical Capacitance vs. Drain-to-Source Voltage**

**Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage**

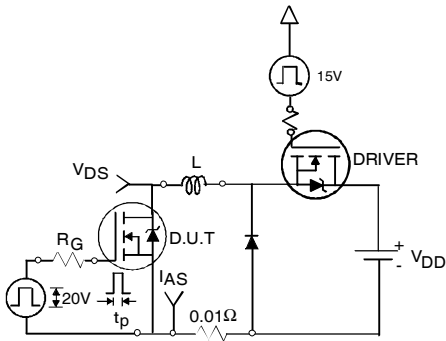

**Fig 7.** Typical Source-Drain Diode Forward Voltage

**Fig 8.** Maximum Safe Operating Area

**Fig 9.** Maximum Drain Current vs. Case Temperature

**Fig 10.** Threshold Voltage vs. Temperature

**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Mounting Base


**Fig 12.** On-Resistance vs. Gate Voltage

**Fig 13.** Maximum Avalanche Energy vs. Drain Current

**Fig 14.** Typical Avalanche Current vs. Pulsewidth

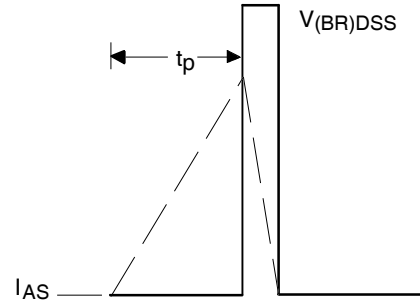


\*  $V_{GS} = 5V$  for Logic Level Devices

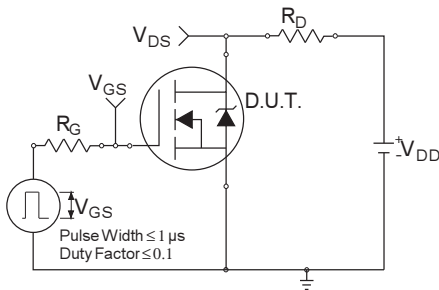
**Fig 15. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs**



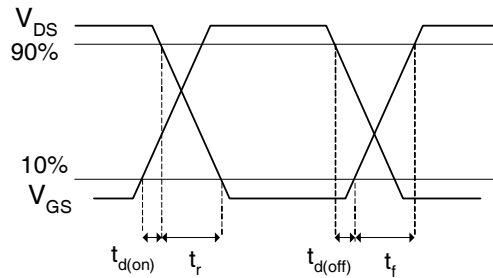
**Fig 16a. Unclamped Inductive Test Circuit**



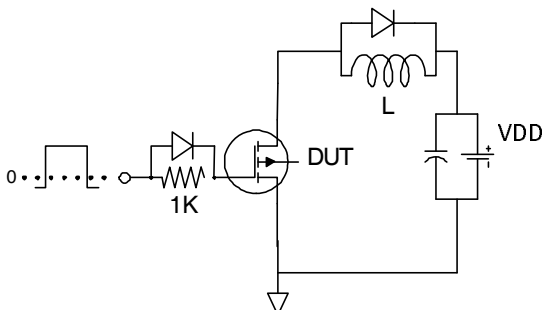
**Fig 16b. Unclamped Inductive Waveforms**



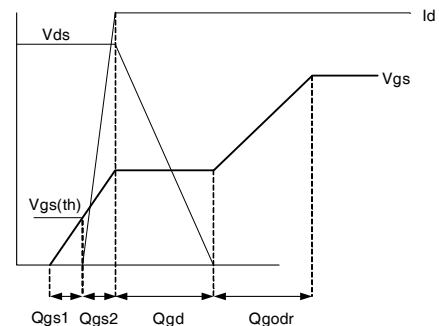
**Fig 17a. Switching Time Test Circuit**



**Fig 17b. Switching Time Waveforms**

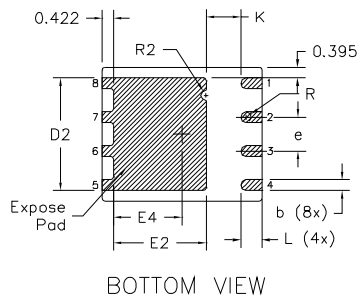
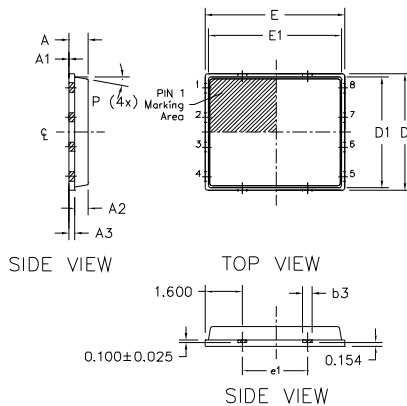


**Fig 18a. Gate Charge Test Circuit**



**Fig 18b. Gate Charge Waveform**

## PQFN 5x6 Outline "B" Package Details

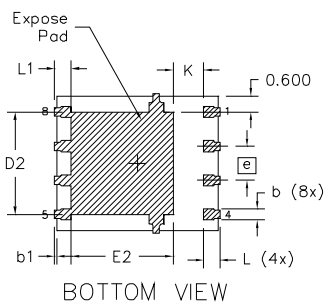
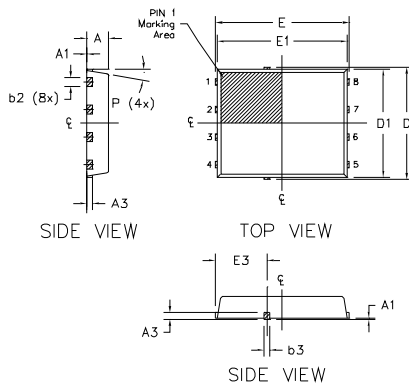


DIM SYMBOL	MILLIMETERS		INCH	
	MIN	MAX	MIN	MAX
A	0.800	0.900	0.0315	0.0543
A1	0.000	0.050	0.0000	0.0020
A3	0.200 REF		0.0079 REF	
b	0.350	0.470	0.0138	0.0185
b1	0.025	0.125	0.0010	0.0049
b2	0.210	0.410	0.0083	0.0161
b3	0.150	0.450	0.0059	0.0177
D	5.000 BSC		0.1969 BSC	
D1	4.750 BSC		0.1870 BSC	
D2	4.100	4.300	0.1614	0.1693
E	6.000 BSC		0.2362 BSC	
E1	5.750 BSC		0.2264 BSC	
E2	3.380	3.780	0.1331	0.1488
e	1.270 REF		0.0500 REF	
e1	2.800 REF		0.1102 REF	
K	1.200	1.420	0.0472	0.0559
L	0.710	0.900	0.0280	0.0354
P	0°	12°	0°	12°
R	0.200 REF		0.0079 REF	
R2	0.150	0.200	0.0059	0.0079

**Note:**

1. Dimensions and tolerancing confirm to ASME Y14.5M-1994
2. Dimension L represents terminal full back from package edge up to 0.1mm is acceptable
3. Coplanarity applies to the expose Heat Slug as well as the terminal
4. Radius on terminal is Optional

## PQFN 5x6 Outline "G" Package Details



DIM SYMBOL	MILLIMETERS		INCH	
	MIN.	MAX.	MIN.	MAX.
A	0.950	1.050	0.0374	0.0413
A1	0.000	0.050	0.0000	0.0020
A3	0.254 REF		0.0100 REF	
b	0.310	0.510	0.0122	0.0201
b1	0.025	0.125	0.0010	0.0049
b2	0.210	0.410	0.0083	0.0161
b3	0.180	0.450	0.0071	0.0177
D	5.150 BSC		0.2028 BSC	
D1	5.000 BSC		0.1969 BSC	
D2	3.700	3.900	0.1457	0.1535
E	6.150 BSC		0.2421 BSC	
E1	6.000 BSC		0.2362 BSC	
E2	3.560	3.760	0.1402	0.1488
E3	2.270	2.470	0.0894	0.0972
e	1.27 REF		0.050 REF	
K	0.830	1.400	0.0327	0.0551
L	0.510	0.710	0.0201	0.0280
L1	0.510	0.710	0.0201	0.0280
P	10 deg	12 deg	0 deg	12 deg

**Note:**

1. Dimensions and tolerancing confirm to ASME Y14.5M-1994
2. Dimension L represents terminal full back from package edge up to 0.1mm is acceptable
3. Coplanarity applies to the expose Heat Slug as well as the terminal
4. Radius on terminal is Optional

For more information on board mounting, including footprint and stencil recommendation, please refer to application note AN-1136:

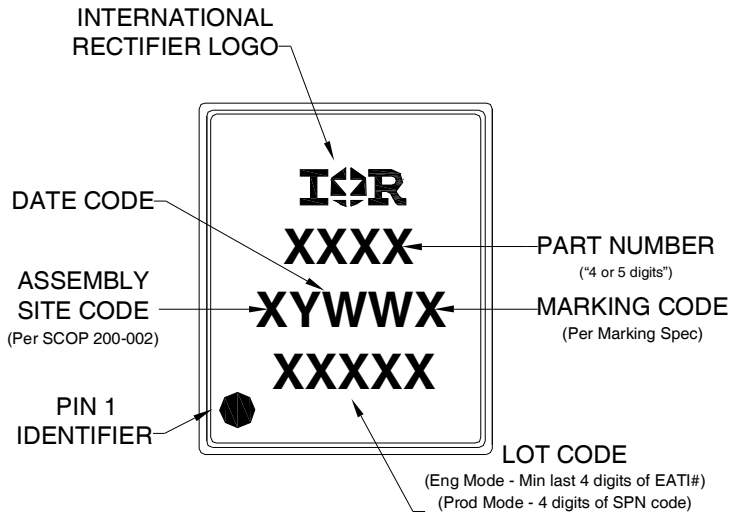
<http://www.irf.com/technical-info/appnotes/an-1136.pdf>

For more information on package inspection techniques, please refer to application note AN-1154:

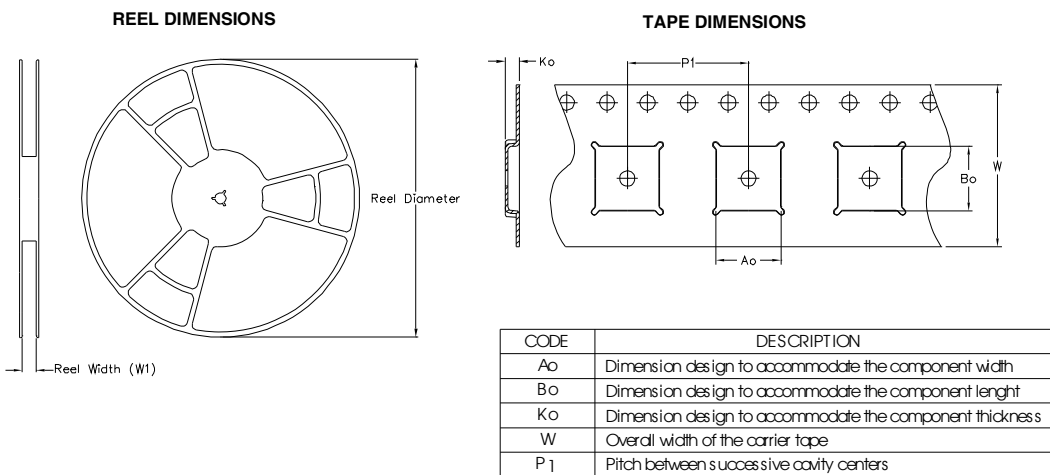
<http://www.irf.com/technical-info/appnotes/an-1154.pdf>

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

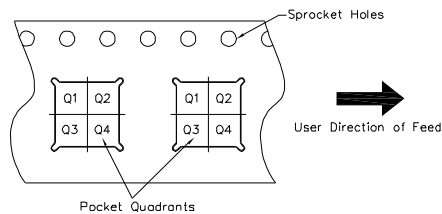
# PQFN 5x6 Part Marking



# PQFN 5x6 Tape and Reel



### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Note: All dimension are nominal

Package Type	Reel Diameter (Inch)	QTY	Reel Width W1 (mm)	Ao (mm)	Bo (mm)	Ko (mm)	P1 (mm)	W (mm)	Pin 1 Quadrant
5 X 6 PQFN	13	4000	12.4	6.300	5.300	1.20	8.00	12	Q1

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>



**Qualification information<sup>†</sup>**

Qualification level	Industrial <sup>††</sup> (per JEDEC JESD47F <sup>†††</sup> guidelines)	
Moisture Sensitivity Level	PQFN 5mm x 6mm	MSL1 (per JEDEC J-STD-020D <sup>†††</sup> )
RoHS compliant	Yes	

† Qualification standards can be found at International Rectifier's web site

<http://www.irf.com/product-info/reliability>

†† Higher qualification ratings may be available should the user have such requirements.

Please contact your International Rectifier sales representative for further information:

<http://www.irf.com/whoto-call/salesrep/>

††† Applicable version of JEDEC standard at the time of product release.

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.41\text{mH}$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 34\text{A}$ .
- ③ Pulse width  $\leq 400\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④  $R_\theta$  is measured at  $T_J$  of approximately  $90^\circ\text{C}$ .
- ⑤ When mounted on 1 inch square 2 oz copper pad on 1.5x1.5 in. board of FR-4 material.

**Revision History**

Date	Comment
4/28/2015	<ul style="list-style-type: none"> <li>• Updated package outline for "option B" and added package outline for "option G" on page 7</li> <li>• Updated tape and reel on page 8.</li> </ul>
5/19/2015	<ul style="list-style-type: none"> <li>• Updated package outline for "option G" on page 7.</li> <li>• Updated "IFX logo" on page 1 and page 9.</li> </ul>

International  
 Rectifier

AN INFINEON TECHNOLOGIES COMPANY

IR WORLD HEADQUARTERS: 101 N. Sepulveda Blvd., El Segundo, California 90245, USA

To contact International Rectifier, please visit <http://www.irf.com/whoto-call/>